

参加費

無料

(事前登録不要)

2011年度IEEE主要ジャーナル・国際会議から
関西発の注目論文を選びすぐり、著者自らに
解説していただきます



日時： 2012年10月26日(金) 10:10~17:45
会場： 大阪大学中之島センター7F 講義室702
(〒530-0005 大阪市北区中之島4-3-53)
URL： <http://www.ieee-jp.org/section/kansai/chapter/eds/>
公用語： 日本語



お問合せ先： IEEE EDS Kansai Chapter Secretary: 小瀧 浩 (シャープ; kotaki.hiroshi@sharp.co.jp)

講演プログラム 2012年10月26日(金) 10:10-17:45

I. CMOSナノデバイス・プロセス・回路

[10:15-11:30]

1. An accurate prediction model of temperature dependent current mismatch in all inversion and influence of subthreshold hump on mismatch characteristics [SSDM2011]
K. Sakakibara (Renesas Electronics)
2. Electric-field-induced band gap of bilayer graphene in ionic liquid [SSDM2011]
Y. Yamashiro (Osaka Univ.)
3. High-mobility Ge-on-insulator p-channel MOSFETs fabricated by lateral liquid-phase epitaxy [SISC2011]
Y. Suzuki (Osaka Univ.)

II. モデリング・信頼性

[13:00-14:15]

1. High reliable strain measurement for power devices using STEM-CBED method [IRPS2011]
N. Nakanishi (Renesas Electronics)
2. Impact of oxidation induced atomic disorder in narrow Si nanowires on transistor performance [Symp. VLSI Tech. 2011]
T. Zushi (Waseda Univ.)
3. Theory of resonant tunneling through a donor state [SSDM2011]
N. Mori (Osaka Univ.)

III. パワー・化合物・量子効果デバイス

[14:25-16:05]

1. CO₂ conversion with light and water by GaN photo-electrode [SSDM2011]
S. Yotsuhashi (Panasonic)
2. GaN-based multi-junction diode with low reverse leakage current using p-type barrier controlling layer [IEDM2011]
D. Shibata (Panasonic)
3. High performance SiC trench devices with ultra-low Ron [IEDM2011]
T. Nakamura (ROHM)
4. Novel SiC power MOSFET with integrated unipolar internal inverse MOS-channel diode [IEDM2011]
M. Uchida (Panasonic)

IV. ディスプレイ・センサ・新規デバイス

[16:15-17:30]

1. Acceleration sensor based on CMOS inverter having force balanced movable gate electrode [SSDM2011]
M. Suzuki (Kansai Univ.)
2. Channel shortening phenomenon due to redox reaction in a lateral direction on In-Ga-Zn-O thin film transistors [AM-FPD2011]
H. Kitakado (Sharp)
3. Mobility improvement in top-gate benzothenobenzothiophene organic transistors processed by spin coating [SSDM2011]
F. Mochizuki (Osaka Pref. Univ.)